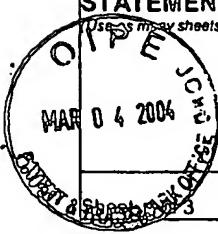


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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(use separate sheets as necessary)

Complete If Known

Application Number	10/042,924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William

Attorney Docket No: 303.684US2

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		Complete if Known Application Number 10/042,924 Filing Date January 9, 2002 First Named Inventor Forbes, Leonard Group Art Unit 2813 Examiner Name Vesperman, William	
Attorney Docket No: 303.684US2			

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		Application Number	10/042,924
		Filing Date	January 9, 2002
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2813
		Examiner Name	Vesperman, William
Attorney Docket No: 303.684US2			

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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William Vesperman

DATE CONSIDERED

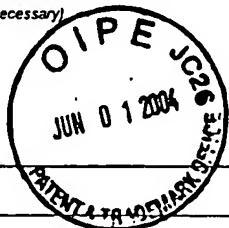
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Sheet 1 of 1

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Application Number	10/042924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William
Attorney Docket No: 303.684US2	

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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